



DSS5240TQ

40V PNP LOW SATURATION TRANSISTOR IN SOT23

Description

This bipolar junction transistor (BJT) is designed to meet the stringent requirement of Automotive Applications.

Features

- BVcEo > -40V
- Ic = -2A High Continuous Collector Current
- Icm = -3A Peak Pulse Current
- Low Saturation Voltage -225mV Max @ Ic = -1A
- $R_{CE(sat)} = 90m\Omega$ at 0.5A for a Low Equivalent On-Resistance
- 730mW Power Dissipation
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DSS5240TQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight 0.008 grams (Approximate)

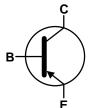
Application

- Gate Driving MOSFETs and IGBTs
- Load Switch
- **DC-DC Converters**
- **Battery Charging**

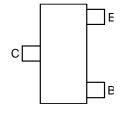
SOT23



Top View



Device Symbol



Top View Pin-Out

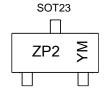
Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DSS5240TQ-7	Automotive	ZP2	7	8	3000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



ZP2 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019)

M = Month (ex: 9 = September)

Date Code Key

Year	2019	2020	2021	2022	202	23 20	24	2025	2026	2027	2028	2029
Code	G	Н		J	K		L	М	N	0	Р	Q
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	VCEO	-40	V
Emitter-Base Voltage	VEBO	-5	V
Peak Pulse Collector Current	Ісм	-3	А
Continuous Collector Current	Ic	-2	A
Base Current	lв	-300	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	730	mW
Power Dissipation (Note 6)	PD	600	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	Reja	171	°C/W
Thermal Resistance, Junction to Ambient Air (Note 6)	Reja	209	°C/W
Thermal Resistance, Junction to Lead (Note 7)	Rejl	75	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

ESD Ratings (Note 8)

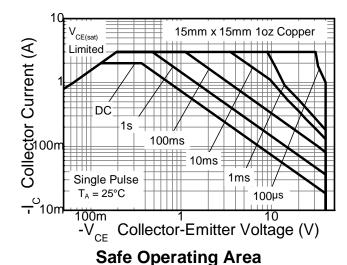
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	С

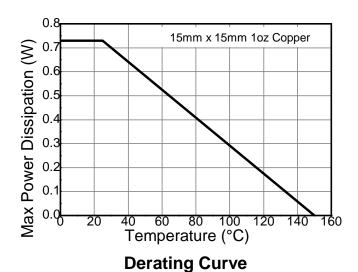
Notes:

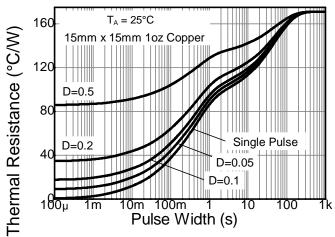
- 5. For a device mounted with the collector lead on 15mm × 15mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 7, except the device is mounted on minimum recommended pad layout.7. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

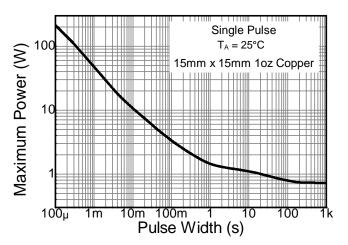


Thermal Characteristics and Derating Information









Transient Thermal Impedance

Pulse Power Dissipation

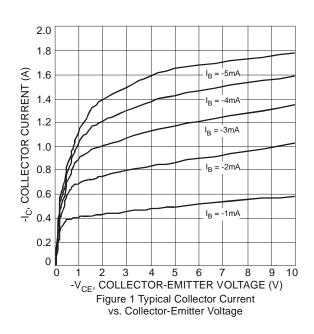


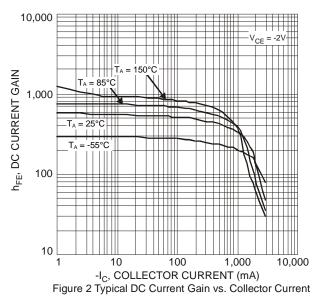
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	ВУсво	-40	_	_	V	Ic = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	BVceo	-40	_	_	V	Ic = -10mA
Emitter-Base Breakdown Voltage	BVEBO	-5	_	_	V	I _E = -100μA
Collector-Base Cutoff Current	lone	_	_	-100	nA	V _{CB} = -30V, I _E = 0
Collector-Base Cutoff Current	Ісво	_	_	-50	μΑ	V _{CB} = -30V, I _E = 0, T _A = +150°C
Emitter-Base Cutoff Current	IEBO	_		-100	nA	V _{EB} = -4V, I _C = 0
ON CHARACTERISTICS (Note 9)						
		300		_		$V_{CE} = -2V, I_{C} = -0.1A$
DC Current Gain	hfe	260	_	_	_	$V_{CE} = -2V, I_{C} = -0.5A$
DC Current Gain		210	_	_		Vce = -2V, Ic = -1A
		100		_		Vce = -2V, Ic = -2A
		_	_	-100	mV	$I_C = -100 \text{mA}, I_B = -1 \text{mA}$
		_	-45	-110		Ic = -500mA, I _B = -50mA
Collector-Emitter Saturation Voltage	VCE(sat)	_		-225		$I_C = -750 \text{mA}, I_B = -15 \text{mA}$
		_		-225		Ic = -1A, I _B = -50mA
		_		-350		I _C = -2A, I _B = -200mA
Equivalent On-Resistance	RcE(sat)	_	90	220	mΩ	Ic = -500mA, I _B = -50mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	_	-1.1	V	Ic = -2A, I _B = -200mA
Base-Emitter Turn-on Voltage	VBE(on)	_	_	-0.75	V	Vce = -2V, Ic = -100mA
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f⊤	100	_	_	MHz	V _{CE} = -10V, I _C = -100mA, f = 100MHz
Output Capacitance	Cobo	_		28	pF	$V_{CB} = -10V$, $f = 1MHz$

9. Measured under pulsed conditions. Pulse width $\leq 300 \mu s.$ Duty cycle $\leq 2\%.$ Note:

Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.) (continued)

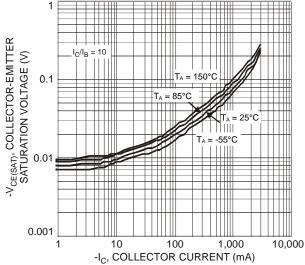


Figure 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

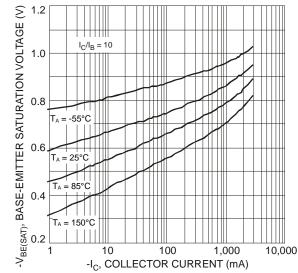


Figure 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

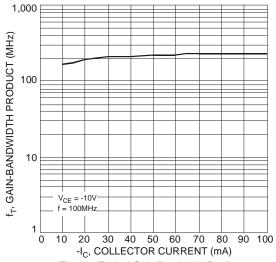
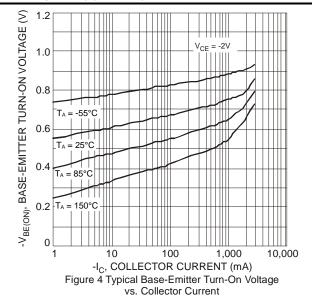


Figure 7 Typical Gain-Bandwidth Product vs. Collector Current

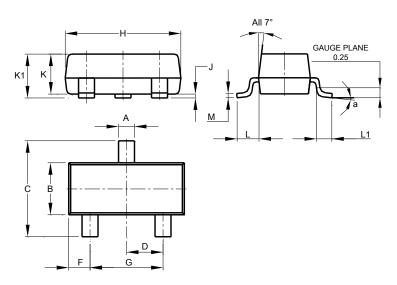




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

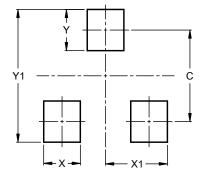


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
M	0.085	0.150	0.110			
а	0°	8°	_			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
V1	2.0



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